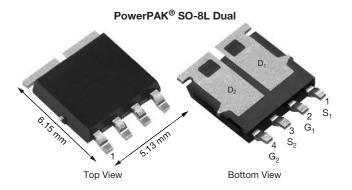
SQJ968EP



Vishay Siliconix

Automotive Dual N-Channel 60 V (D-S) 175 °C MOSFET

PRODUCT SUMMARY	
V _{DS} (V)	60
$R_{DS(on)} (\Omega)$ at $V_{GS} = 10 V$	0.0336
$R_{DS(on)} (\Omega)$ at $V_{GS} = 4.5 V$	0.0444
I _D (A) per leg	23.5
Configuration	Dual
Package	PowerPAK SO-8L

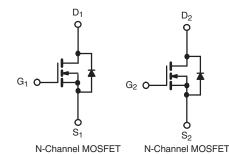


FEATURES

- TrenchFET[®] power MOSFET
- AEC-Q101 qualified
- 100 % R_q and UIS tested
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>



RoHS COMPLIANT HALOGEN FREE



ABSOLUTE MAXIMUM RATING	S (T _C = 25 °C, unles	s otherwise noted)	
PARAMETER		SYMBOL	LIMIT	UNIT
Drain-Source Voltage		V _{DS}	60	v
Gate-Source Voltage	V _{GS}	± 20	v	
Continuous Drain Current ^a	T _C = 25 °C	1	23.5	
	T _C = 125 °C	I _D	13.5	
Continuous Source Current (Diode Conduct	I _S	23	А	
Pulsed Drain Current ^b	I _{DM}	72		
Single Pulse Avalanche Current	L = 0.1 mH	I _{AS}	9	
Single Pulse Avalanche Energy		E _{AS}	4	mJ
Martin an Daria a Dirata di a b	T _C = 25 °C	Р	42	w
Maximum Power Dissipation ^b	T _C = 125 °C	P _D	14	vv
Operating Junction and Storage Temperature	T _J , T _{stg}	-55 to +175	°C	
Soldering Recommendations (Peak Tempera	ature) ^{d, e}		260	

THERMAL RESISTANCE RATINGS				
PARAMETER		SYMBOL	LIMIT	UNIT
Junction-to-Ambient	PCB Mount ^c	R _{thJA}	85	°C/W
Junction-to-Case (Drain)		R _{thJC}	3.5	C/W

Notes

- a. Package limited.
- b. Pulse test; pulse width \leq 300 $\mu s,$ duty cycle \leq 2 %.
- c. When mounted on 1" square PCB (FR4 material).

d. See solder profile (<u>www.vishay.com/doc?73257</u>). The PowerPAK SO-8L is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection.

e. Rework conditions: manual soldering with a soldering iron is not recommended for leadless components.

1

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PARAMETER	SYMBOL	TES	MIN.	TYP.	MAX.	UNIT	
Static					•		
Drain-Source Breakdown Voltage	V _{DS}	V _{GS} =	$V_{GS} = 0 V, I_{D} = 250 \mu A$		-	-	V
Gate-Source Threshold Voltage	V _{GS(th)}	V _{DS} =	= V _{GS} , I _D = 250 μΑ	1.5	2.0	2.5	v
Gate-Source Leakage	I _{GSS}	V _{DS} =	: 0 V, V _{GS} = ± 20 V	-	-	± 100	nA
		$V_{GS} = 0 V$	V _{DS} = 60 V	-	-	1	
Zero Gate Voltage Drain Current	I _{DSS}	$V_{GS} = 0 V$	V _{DS} = 60 V, T _J = 125 °C	-	-	50	μA
		$V_{GS} = 0 V$	V _{DS} = 60 V, T _J = 175 °C	-	-	150	$ \begin{array}{c c} & V \\ 5 & V \\ \hline 5 & & V \\ \hline 0 & & nA \\ \hline 0 & & \mu A \\ \hline 0 & & & \mu A \\ \hline 0 & & & & & \\ \hline 14 & & & & & \\ \hline 15 & & & & & \\ \hline 15 & & & & & \\ \hline 16 & & & & & \\ 16 & & & & & \\ \hline 16 & & & & & \\ 16 & & & & $
On-State Drain Current ^a	I _{D(on)}	$V_{GS} = 10 V$	$V_{DS} \ge 5 V$	30	-	-	Α
		$V_{GS} = 10 V$	I _D = 4.8 A	-	0.0280	0.0336	
Durin Source On State Desistance a	Б	$V_{GS} = 10 V$	I _D = 4.8 A, T _J = 125 °C	-	-	0.0900	
Drain-Source On-State Resistance ^a	R _{DS(on)}	V _{GS} = 10 V	I _D = 4.8 A, T _J = 175 °C	-	-	0.1430	0.0336 Ω 0.0900 Ω 0.1430 Ω 0.0444 S 714 pF 48 PF
		$V_{GS} = 4.5 V$	I _D = 4.2 A	-	0.0370	0.0444	
Forward Transconductance ^b	g _{fs}	V _{DS} = 15 V, I _D = 4.8 A		-	16	-	S
Dynamic ^b		•		•		•	
Input Capacitance	C _{iss}		V _{DS} = 30 V, f = 1 MHz	-	571	714	pF
Output Capacitance	C _{oss}	$V_{GS} = 0 V$		-	98	123	
Reverse Transfer Capacitance	C _{rss}			-	38	48	
Total Gate Charge ^c	Qg			-	12.3	18.5	
Gate-Source Charge ^c	Q _{gs}	$V_{GS} = 10 V$	$V_{DS} = 30 \text{ V}, I_D = 4.5 \text{ A}$	-	1.9	-	nC
Gate-Drain Charge ^c	Q _{gd}			-	2.6	-	
Gate Resistance	R _g	f = 1 MHz		1.3	-	6	Ω
Turn-On Delay Time ^c	t _{d(on)}			-	8	12	
Rise Time ^c	t _r	$\label{eq:VDD} \begin{array}{l} V_{\text{DD}} = 30 \text{ V}, \ R_{\text{L}} = 30 \ \Omega \\ I_{\text{D}} \cong 1 \text{ A}, \ V_{\text{GEN}} = 10 \text{ V}, \ R_{\text{g}} = 1 \ \Omega \end{array}$		-	9	13.5	ns
Turn-Off Delay Time ^c	t _{d(off)}			-	19.5	29	
Fall Time ^c	t _f			-	6.5	10	
Source-Drain Diode Ratings and Chara	acteristics ^b	·			•		
Pulsed Current ^a	I _{SM}			-	-	32	Α
Forward Voltage	V _{SD}	I _F = 3.1 A, V _{GS} = 0 V		-	0.8	1.1	V

Notes

a. Pulse test; pulse width \leq 300 $\mu s,$ duty cycle \leq 2 %.

b. Guaranteed by design, not subject to production testing.

c. Independent of operating temperature.

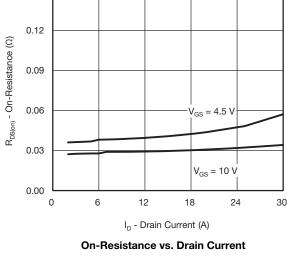
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

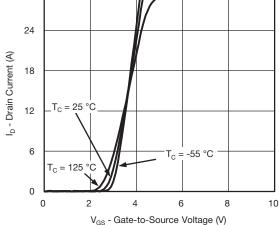
2

T_C = 125 °C T_C -55 °C 0 3 4 5 0 1 2 1 2 V_{GS} - Gate-to-Source Voltage (V) **Transfer Characteristics** 1000

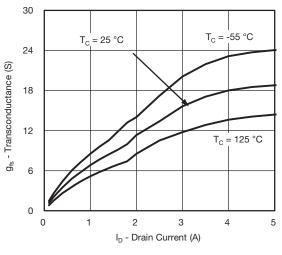
$V_{GS} = 3 V$ 0 8 10 6 0 2 V_{DS} - Drain-to-Source Voltage (V) **Output Characteristics** 30

30

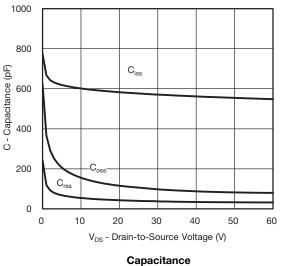








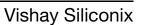




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For technical questions, contact: automostechsupport@vishay.com





V_{GS} = 10 V thru 5 V

 $V_{GS} = 4 V$

4

°C $\Gamma_{\rm C} = 25$

24

18

12

6

0

10.0

8.0

6.0

4.0

2.0

0.0

0.15

0

l_D - Drain Current (A)

0

2

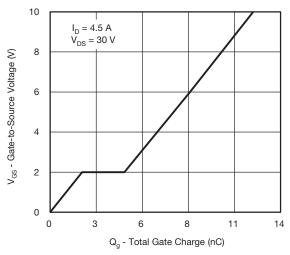
I_D - Drain Current (A)

TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted) 30

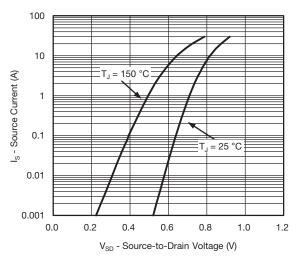
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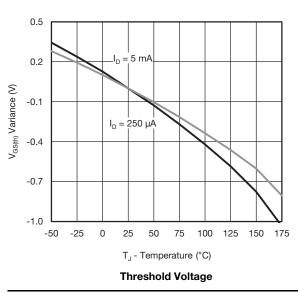
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)

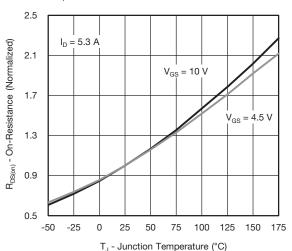




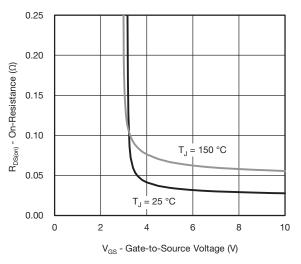


Source Drain Diode Forward Voltage

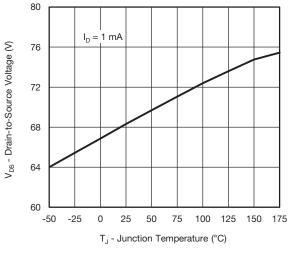




On-Resistance vs. Junction Temperature



On-Resistance vs. Gate-to-Source Voltage



Drain Source Breakdown vs. Junction Temperature

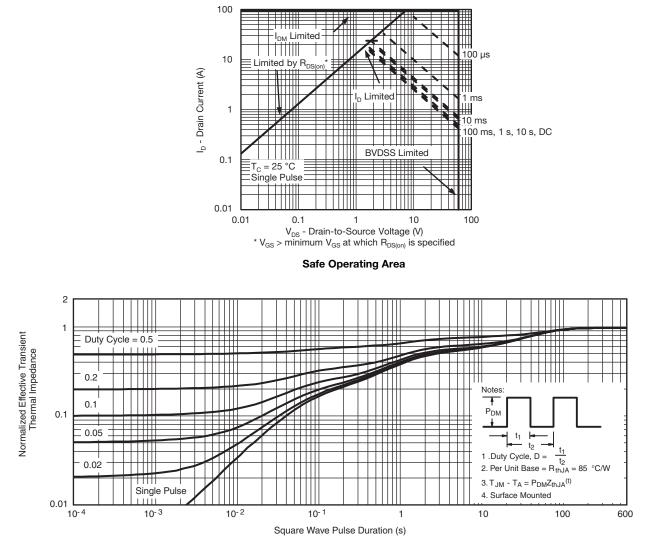
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THERMAL RATINGS ($T_A = 25 \text{ °C}$, unless otherwise noted)



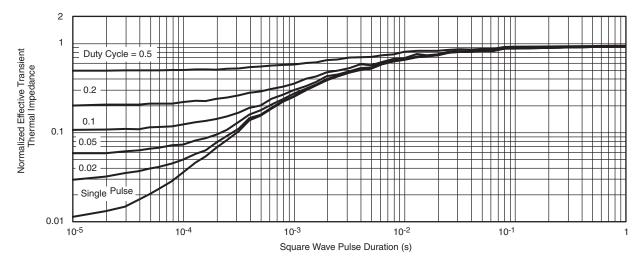
Normalized Thermal Transient Impedance, Junction-to-Ambient



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THERMAL RATINGS (T_A = 25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Case

Note

• The characteristics shown in the two graphs

- Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)

- Normalized Transient Thermal Impedance Junction-to-Case (25 °C)

are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishay.com/ppg?62817.



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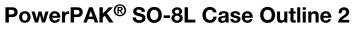
REVISION HISTORY^a

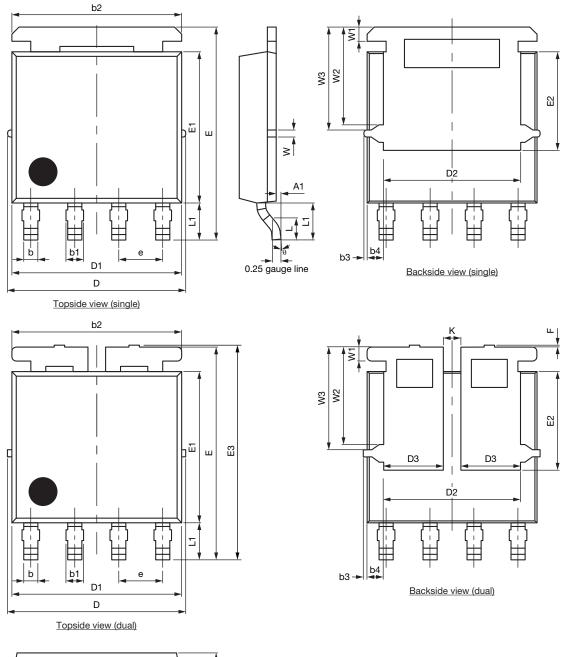
NEVISION	moroni	
REVISION	DATE	DESCRIPTION OF CHANGE
В	04-Aug-15	Revised R _g minimum limit
С	14-Jun-16	• I _D and P _D corrected

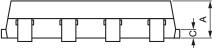
Note

a. As of April 2014









Package Information



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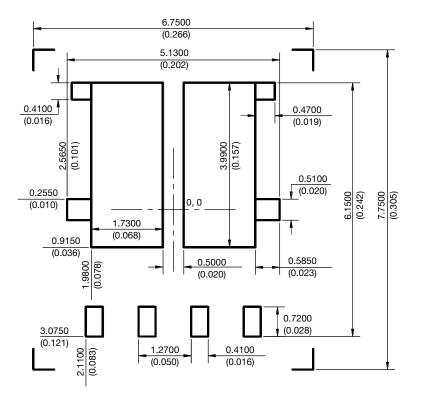
DIM.	MILLIMETERS			INCHES				
	MIN.	NOM.	MAX.	MIN.	NOM.	MAX		
А	1.00	1.07	1.14	0.039	0.042	0.045		
A1	0.00	-	0.127	0.00	-	0.005		
b	0.33	0.41	0.48	0.013	0.016	0.019		
b1	0.44	0.51	0.58	0.017	0.020	0.023		
b2	4.80	4.90	5.00	0.189	0.193	0.197		
b3		0.094			0.004			
b4		0.47			0.019			
С	0.20	0.25	0.30	0.008	0.010	0.012		
D	5.00	5.13	5.25	0.197	0.202	0.207		
D1	4.80	4.90	5.00	0.189	0.193	0.197		
D2	3.86	3.96	4.06	0.152	0.156	0.160		
D3	1.63	1.73	1.83	0.064	0.068	0.072		
е		1.27 BSC			0.050 BSC			
E	6.05	6.15	6.25	0.238	0.242	0.246		
E1	4.27	4.37	4.47	0.168	0.172	0.176		
E2	2.75	2.85	2.95	0.108	0.112	0.116		
E3	6.05	6.22	6.40	0.238	0.245	0.252		
F	-	-	0.15	-	-	0.006		
L	0.62	0.72	0.82	0.024	0.028	0.032		
L1	0.92	1.07	1.22	0.036	0.042	0.048		
К		0.51			0.020			
W		0.23			0.009			
W1	0.41			0.016				
W2		2.82			0.111			
W3		2.96			0.117			
θ	0°	-	10°	0°	-	10°		

Note

• Millimeters will govern



RECOMMENDED MINIMUM PAD FOR PowerPAK® SO-8L DUAL



Recommended Minimum Pads Dimensions in mm (inches) Keep-out 6.75 (0.266) x 7.75 (0.305)

Revision: 07-Feb-12



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